

## AMENDMENTS TO SPECIFICATIONS ARE AS FOLLOWS:

page 1, line 14:

the thickness variations of pad oxide, which may be in the range of 30-50 °A Å, the long channel

page 5, line 12, line 13, and line 15:

approximately about 25 – 120 °A Å thick and pad nitride 14 in the range of approximately about

500 – 2000 °A Å thick; using a plasma process, pattern the pad nitride using a resist mask; using

... shallow trench, in the range of approximately about 2000-5000 °A Å using suitable plasma ...

page 6, line 12:

implantation is shown in Figure 4 for two pad oxide thicknesses of 50 and 100 °A Å. It is clear ...

page 7, line 5 and line 10:

variation for pad oxide thickness variation in the range of 35 – 110 °A Å is 0.489 +/- 0.0327volts

<b>Pad Oxide Thickness, °A <u>Å</u></b>	110	100	90	80	70	60	35	0
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page 8, line 3:

°A Å of equivalent silicon dioxide thickness.